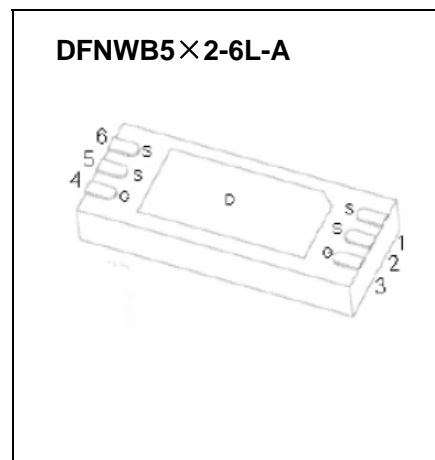


DFNWB5×2-6L-A Plastic-Encapsulate MOSFETS

CJND8804 Dual N-Channel MOSFET

DESCRIPTION

The CJND8804 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. It is ESD protected. This device is suitable for use as a uni-directional or bi-directional load switch, facilitated by its common-drain configuration.



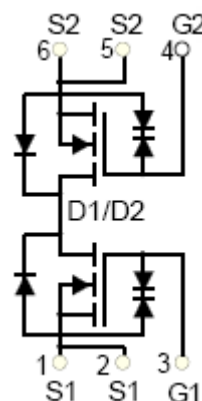
MARKING:



FRONT SIDE



BACK SIDE



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	8	A
Pulsed Drain Current	I_{DM}^*	30	A
Thermal Resistance from Junction to Ambient(note1)	$R_{\theta JA}$	175	$^{\circ}\text{C/W}$
Thermal Resistance from Junction to Ambient(note2)		70	$^{\circ}\text{C/W}$
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}\text{C}$

*Repetitive rating: Pulse width limited by junction temperature.

Note: 1. When mounted on a minimum pad.

2. When mounted on 1 in² of 2oz copper board.

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 16V, V _{GS} = 0V			10	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±10	μA
Gate threshold voltage (note 1)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5		1	V
Drain-source on-resistance (note 1)	R _{DS(on)}	V _{GS} = 10V, I _D = 8A			13	mΩ
		V _{GS} = 4.5V, I _D = 5A			14	mΩ
		V _{GS} = 3.8V, I _D = 5A			15.5	mΩ
		V _{GS} = 2.5V, I _D = 4A			19	mΩ
		V _{GS} = 1.8V, I _D = 3A			27	mΩ
Forward tranconductance (note 1)	g _{FS}	V _{DS} = 5V, I _D = 8A		36		S
Diode forward voltage(note 1)	V _{SD}	I _S = 1A, V _{GS} = 0V			1	V
DYNAMIC PARAMETERS (note 2)						
Input Capacitance	C _{iSS}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz		1800		pF
Output Capacitance	C _{oSS}			230		pF
Reverse Transfer Capacitance	C _{rSS}			200		pF
Total gate charge	Q _g	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 8A		17.9		nC
Gate-source charge	Q _{gs}			1.5		nC
Gate-drain charge	Q _{gd}			4.7		nC
SWITCHING PARAMETERS (note 2)						
Turn-on delay time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 10V, R _L = 1.2Ω, R _{GEN} = 3Ω		2.5		ns
Turn-on rise time	t _r			7.2		ns
Turn-off delay time	t _{d(off)}			49		ns
Turn-off fall time	t _f			10.8		ns

Notes :

1. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 0.5%.
2. Guaranteed by design, not subject to production testing.